

# DATA SHEET

**BU4508AF**

**Silicon Diffused Power Transistor**

Product specification  
Supersedes data of January 1998  
File under Discrete Semiconductors, SC06

June 1998

## Silicon Diffused Power Transistor

BU4508AF

## GENERAL DESCRIPTION

Enhanced performance, new generation, high-voltage, high-speed switching npn transistor in a plastic full-pack envelope intended for use in horizontal deflection circuits of colour television receivers and p.c. monitors. Features exceptional tolerance to base drive and collector current load variations resulting in a very low worst case dissipation.

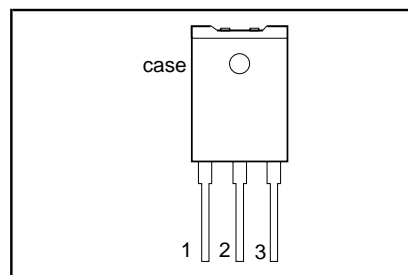
## QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	800	V
$I_C$	Collector current (DC)		-	8	A
$I_{CM}$	Collector current peak value		-	15	A
$P_{tot}$	Total power dissipation	$T_{hs} \leq 25\text{ }^\circ\text{C}$	-	45	W
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.25\text{ A}$	-	3.0	V
$I_{Csat}$	Collector saturation current	$f = 16\text{ kHz}$	5.0	-	A
		$f = 64\text{ kHz}$	4.0	-	A
$t_f$	Fall time	$I_{Csat} = 5\text{ A}; f = 16\text{ kHz}$	0.35	0.48	$\mu\text{s}$
		$I_{Csat} = 4\text{ A}; f = 64\text{ kHz}$	0.17	-	$\mu\text{s}$

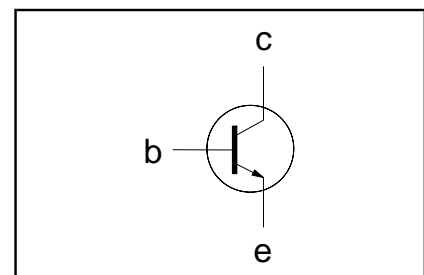
## PINNING - SOT199

PIN	DESCRIPTION
1	base
2	collector
3	emitter
case	isolated

## PIN CONFIGURATION



## SYMBOL



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CESM}$	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
$V_{CEO}$	Collector-emitter voltage (open base)		-	800	V
$I_C$	Collector current (DC)		-	8	A
$I_{CM}$	Collector current peak value		-	15	A
$I_B$	Base current (DC)		-	4	A
$I_{BM}$	Base current peak value		-	6	A
$-I_{BM}$	Reverse base current peak value <sup>1</sup>		-	5	A
$P_{tot}$	Total power dissipation	$T_{hs} \leq 25\text{ }^\circ\text{C}$	-	45	W
$T_{stg}$	Storage temperature		-55	150	$^\circ\text{C}$
$T_j$	Junction temperature		-	150	$^\circ\text{C}$

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Junction to heatsink	with heatsink compound	-	2.8	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	35	-	K/W

<sup>1</sup> Turn-off current.

## Silicon Diffused Power Transistor

BU4508AF

## ISOLATION LIMITING VALUE &amp; CHARACTERISTIC

 $T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{isol}$	Repetitive peak voltage from all three terminals to external heatsink	R.H. $\leq 65\%$ ; clean and dustfree	-	-	2500	V
$C_{isol}$	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	22	-	pF

## STATIC CHARACTERISTICS

 $T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CES}$	Collector cut-off current <sup>2</sup>	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	-	-	1.0	mA
$I_{CES}$		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	2.0	mA
$I_{EBO}$	Emitter cut-off current	$V_{EB} = 6.0\text{ V}; I_C = 0\text{ A}$	-	-	100	$\mu\text{A}$
$BV_{EBO}$	Emitter-base breakdown voltage	$I_B = 1\text{ mA}$	7.5	13.5	-	V
$V_{CEOsust}$	Collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 100\text{ mA};$ $L = 25\text{ mH}$	800	-	-	V
$V_{CEsat}$	Collector-emitter saturation voltages	$I_C = 5.0\text{ A}; I_B = 1.25\text{ A}$	-	-	3.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C = 5.0\text{ A}; I_B = 1.25\text{ A}$	0.85	0.94	1.03	V
$h_{FE}$	DC current gain	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V}$	-	12	-	
$h_{FE}$		$I_C = 5.0\text{ A}; V_{CE} = 5\text{ V}$	4.2	5.7	7.3	

## DYNAMIC CHARACTERISTICS

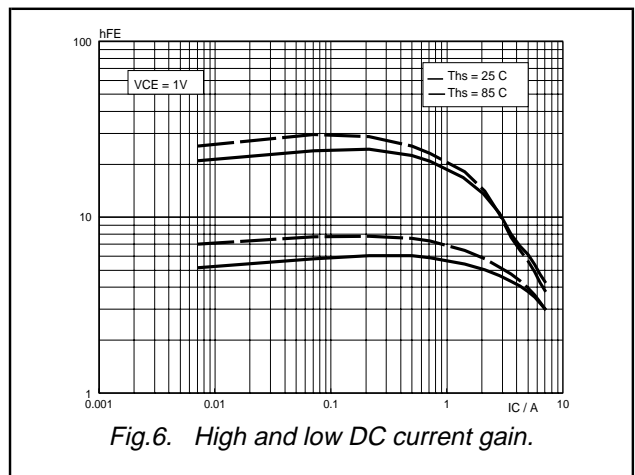
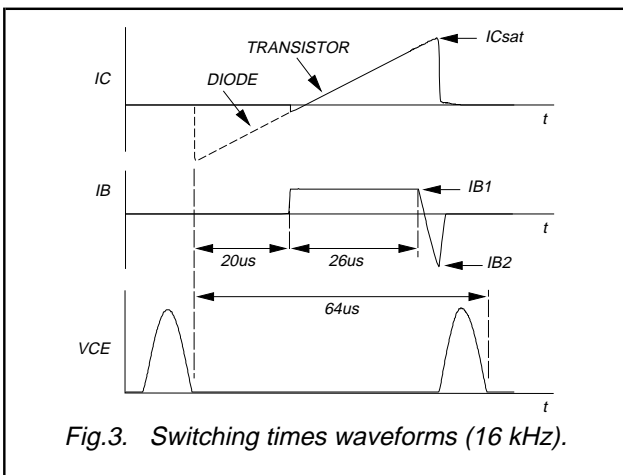
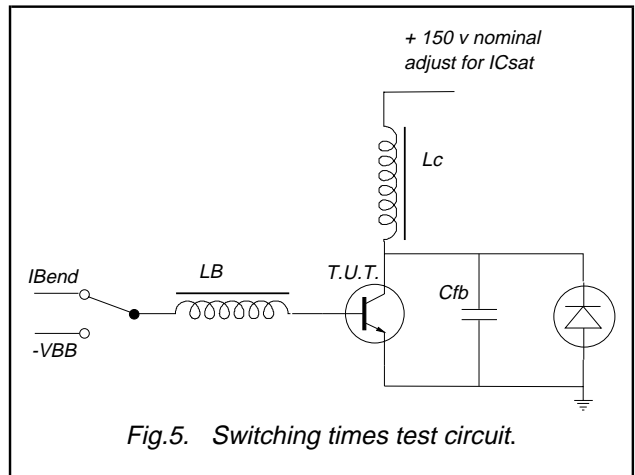
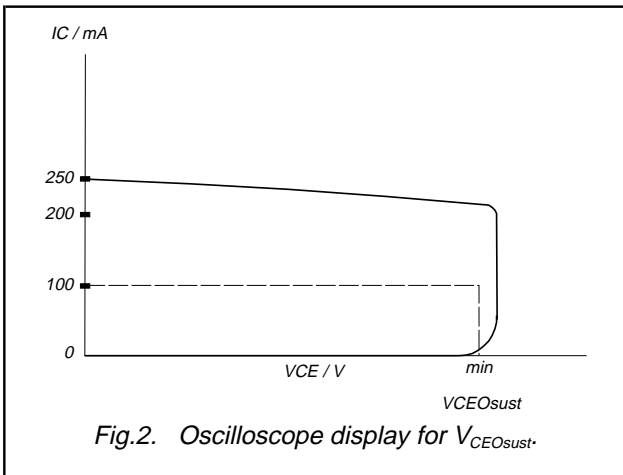
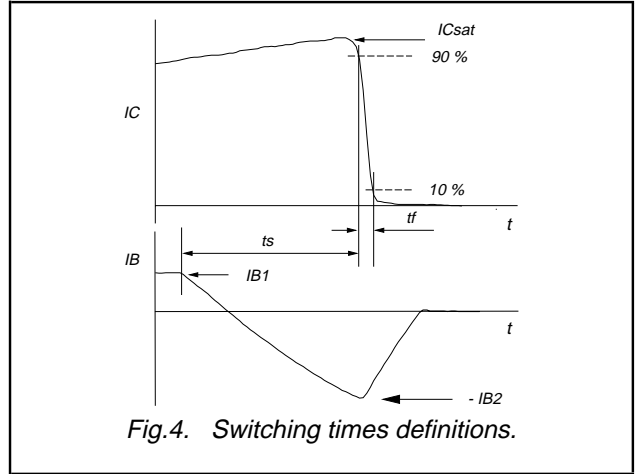
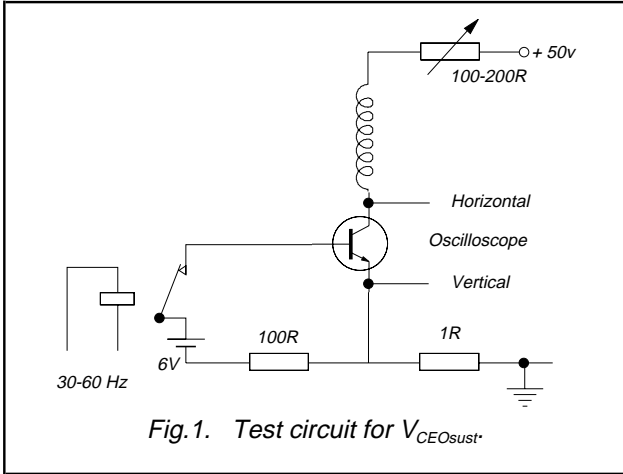
 $T_{hs} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$C_c$	Collector capacitance	$I_E = 0\text{ A}; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	80	-	pF
$t_s$	Switching times (16 kHz line deflection circuit) Turn-off storage time	$I_{Csat} = 5.0\text{ A}; I_{B1} = 1.0\text{ A}; (I_{B2} = -2.5\text{ A})$	3.2	4.3	$\mu\text{s}$
$t_f$	Turn-off fall time		0.35	0.48	$\mu\text{s}$
$t_s$	Switching times (64 kHz line deflection circuit) Turn-off storage time	$I_{Csat} = 4\text{ A}; I_{B1} = 0.8\text{ A}; (I_{B2} = -2.0\text{ A})$	1.9	-	$\mu\text{s}$
$t_f$	Turn-off fall time		0.17	-	$\mu\text{s}$

<sup>2</sup> Measured with half sine-wave voltage (curve tracer).

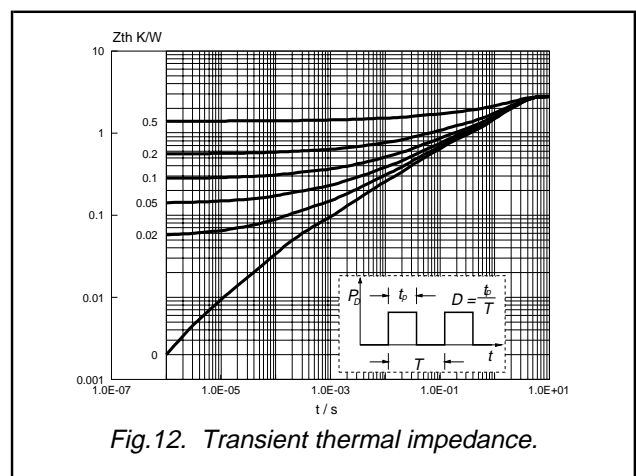
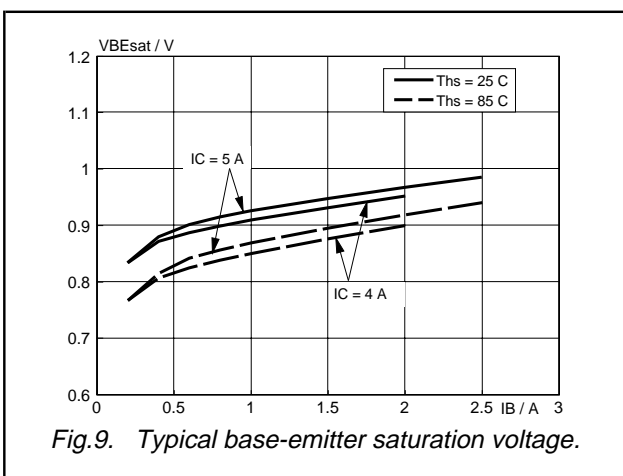
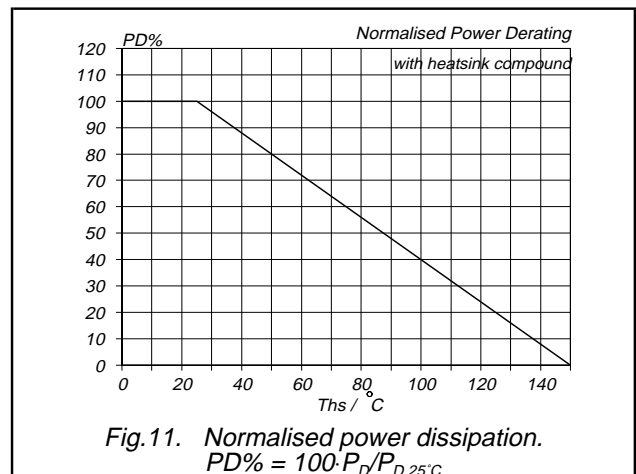
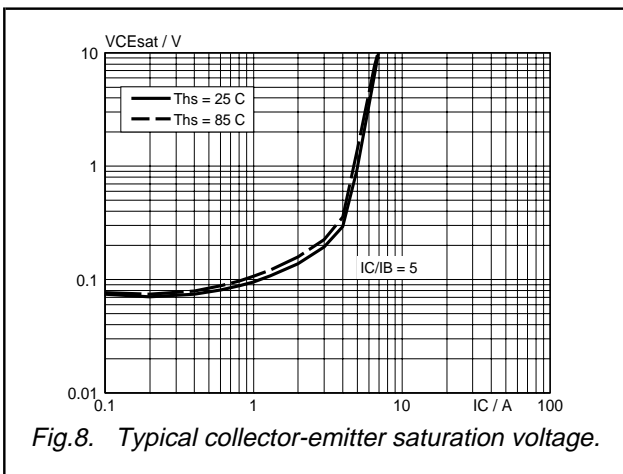
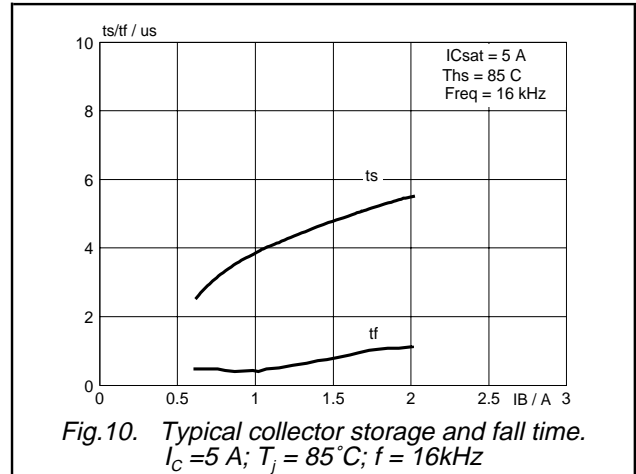
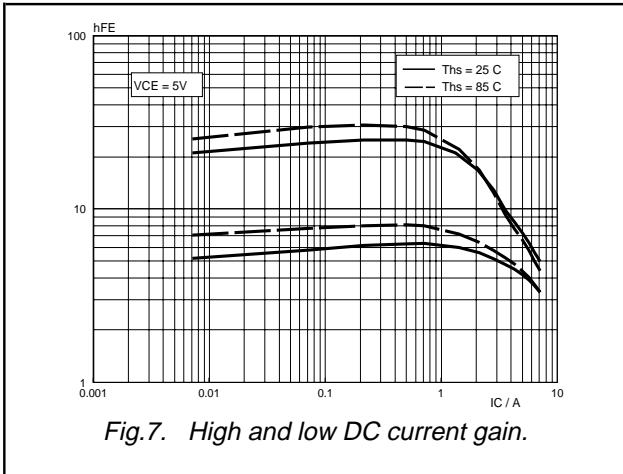
Silicon Diffused Power Transistor

BU4508AF



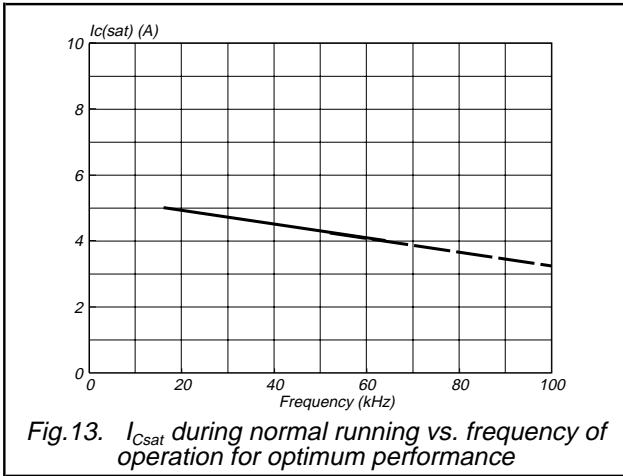
Silicon Diffused Power Transistor

BU4508AF



Silicon Diffused Power Transistor

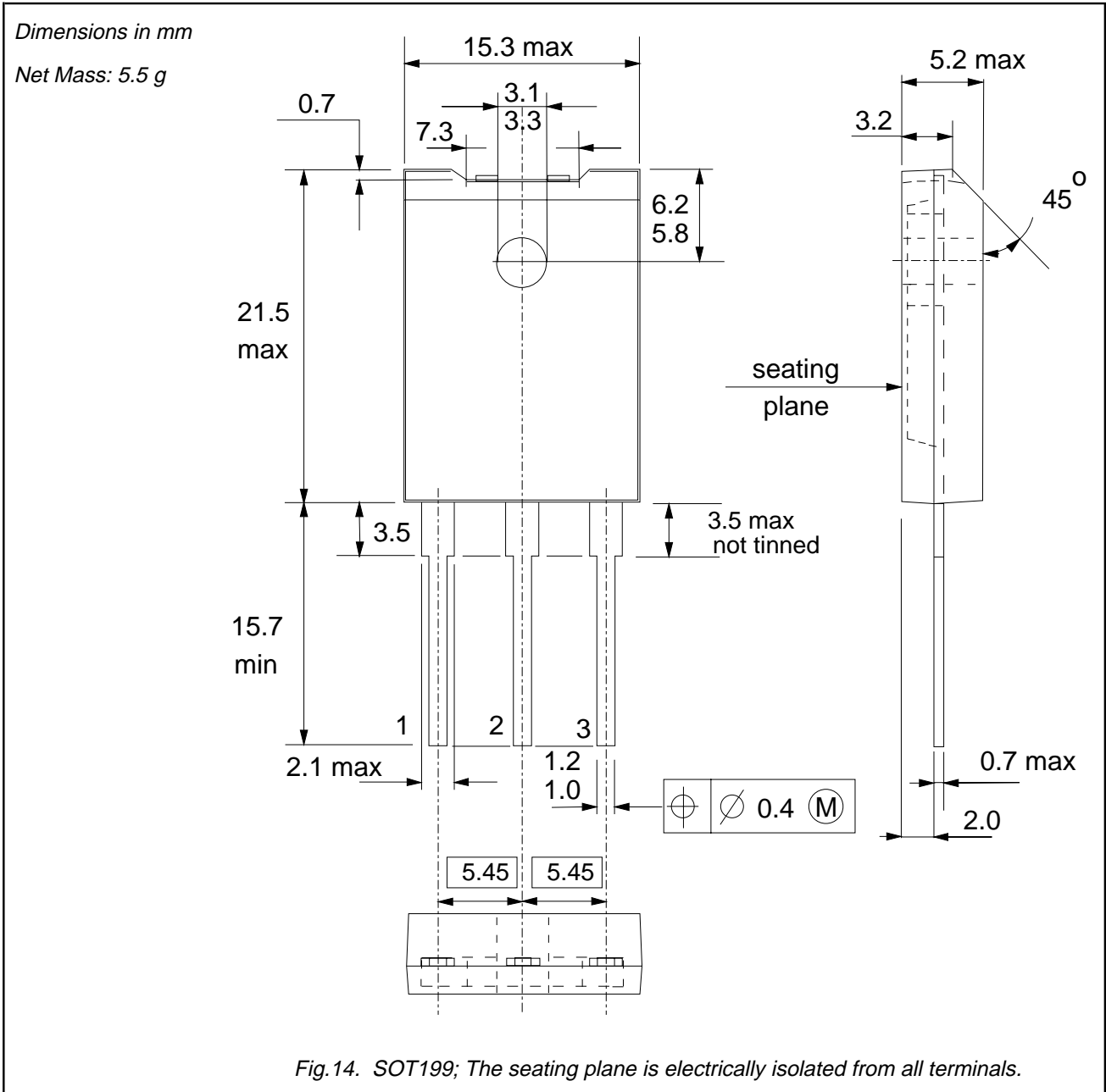
BU4508AF



Silicon Diffused Power Transistor

BU4508AF

**MECHANICAL DATA**



**Notes**

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

## Silicon Diffused Power Transistor

BU4508AF

**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
<b>© Philips Electronics N.V. 1998</b>	
All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.	
The information presented in this document does not form part of any quotation or contract, it is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.	

**LIFE SUPPORT APPLICATIONS**

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.



Silicon Diffused Power Transistor

BU4508AF

---

**NOTES**

Silicon Diffused Power Transistor

BU4508AF

---

NOTES

Silicon Diffused Power Transistor

BU4508AF

---

NOTES

# Philips Semiconductors – a worldwide company

**Argentina:** see South America

**Australia:** 34 Waterloo Road, NORTH RYDE, NSW 2113, Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010, Fax. +43 160 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

**Belgium:** see The Netherlands

**Brazil:** see South America

**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor, 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS, Tel. +1 800 234 7381

**China/Hong Kong:** 501 Hong Kong Industrial Technology Centre, 72 Tat Chee Avenue, Kowloon Tong, HONG KONG, Tel. +852 2319 7888, Fax. +852 2319 7700

**Colombia:** see South America

**Czech Republic:** see Austria

**Denmark:** Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S, Tel. +45 32 88 2636, Fax. +45 31 57 0044

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920

**France:** 51 Rue Carnot, BP317, 92156 SURESNES Cedex, Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS/ATHENS, Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025, Tel. +91 22 493 8541, Fax. +91 22 493 0966

**Indonesia:** PT Philips Development Corporation, Semiconductors Division, Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510, Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

**Ireland:** Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905, Tel. +9-5 800 234 7381

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB, Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO, Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Pakistan:** see Singapore

**Philippines:** Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Ul. Lukiska 10, PL 04-123 WARSZAWA, Tel. +48 22 612 2831, Fax. +48 22 612 2327

**Portugal:** see Spain

**Romania:** see Italy

**Russia:** Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW, Tel. +7 095 755 6918, Fax. +7 095 755 6919

**Singapore:** Lorong 1, Toa Payoh, SINGAPORE 319762, Tel. +65 350 2538, Fax. +65 251 6500

**Slovakia:** see Austria

**Slovenia:** see Italy

**South Africa:** S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale, 2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000, Tel. +27 11 470 5911, Fax. +27 11 470 5494

**South America:** Al. Vicente Pinzon, 173, 6th floor, 04547-130 SÃO PAULO, SP, Brazil, Tel. +55 11 821 2333, Fax. +55 11 821 2382

**Spain:** Balmes 22, 08007 BARCELONA, Tel. +34 93 301 6312, Fax. +34 93 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM, Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH, Tel. +41 1 488 2741 Fax. +41 1 488 3263

**Taiwan:** Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1, TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874

**Thailand:** PHILIPS ELECTRONICS (THAILAND) Ltd., 209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260, Tel. +66 2 745 4090, Fax. +66 2 398 0793

**Turkey:** Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL, Tel. +90 212 279 2770, Fax. +90 212 282 6707

**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7, 252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409, Tel. +1 800 234 7381

**Uruguay:** see South America

**Vietnam:** see Singapore

**Yugoslavia:** PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD, Tel. +381 11 625 344, Fax. +381 11 635 777

**For all other countries apply to:** Philips Semiconductors, International Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

**Internet:** <http://www.semiconductors.philips.com>

© Philips Electronics N.V. 1998

SCA60

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

135104/150/03/pp12

Date of release: June 1998

Document order number: 9397 750 04011

*Let's make things better.*

**Philips  
Semiconductors**



**PHILIPS**